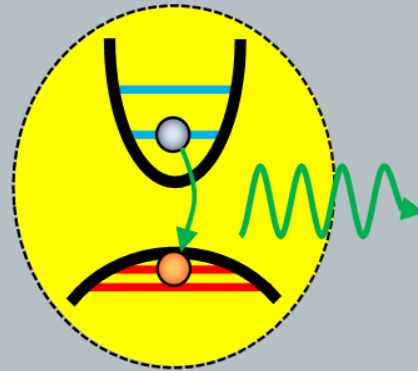
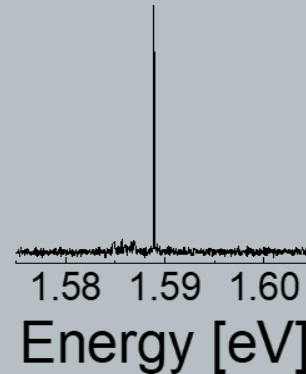


INF18 - Photolumineszenz von Halbleiter-Quantenpunkten

Christian Heyn, Center for Hybrid Nanostructures (CHyN), University of Hamburg



Quantum dot

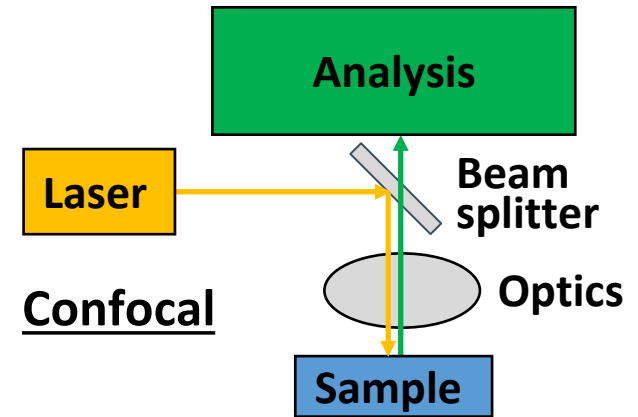


Luminescence: „cold light“

Photoluminescence: inelastic light scattering

Photoluminescence (PL) spectroscopy:

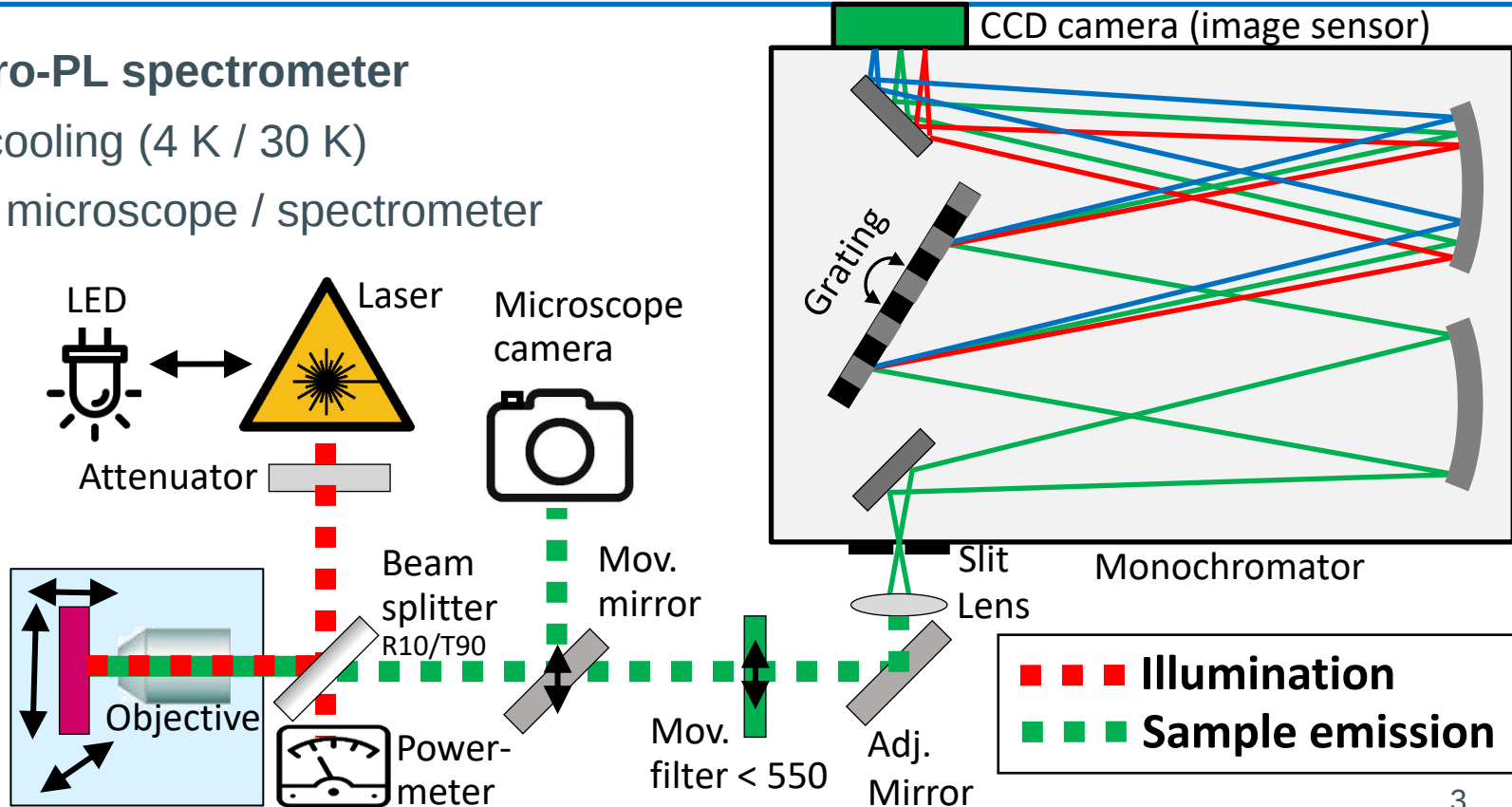
- Excitation by laser
- Confocal geometry for high resolution: excitation / emission through one objective
- Spectral analysis of the reflected emission
- Information: energy of states inside the sample
- Here: PL on semiconductor quantum dots (QDs)



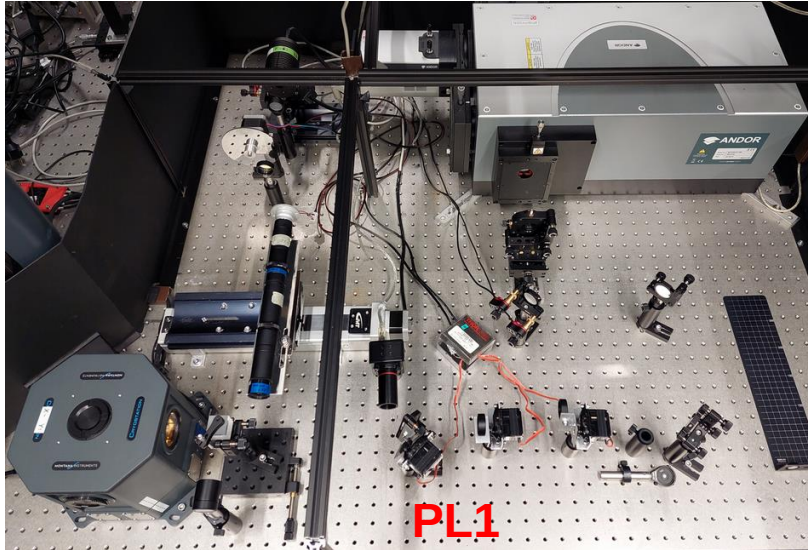
INF18 - Photolumineszenz von Halbleiter-Quantenpunkten

Basic micro-PL spectrometer

- Sample cooling (4 K / 30 K)
- Confocal microscope / spectrometer

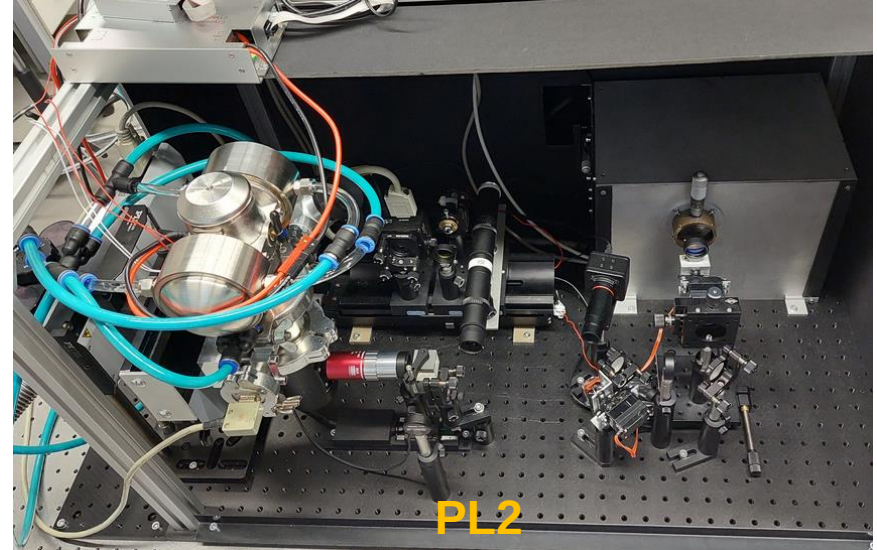


INF18 - Photolumineszenz von Halbleiter-Quantenpunkten



PL1 (state of the art setup)

- Sample cooling down to 3 K
- Ultra-low vibrations (< 1 nm)
- Extensions: high resolution, lifetime, ...



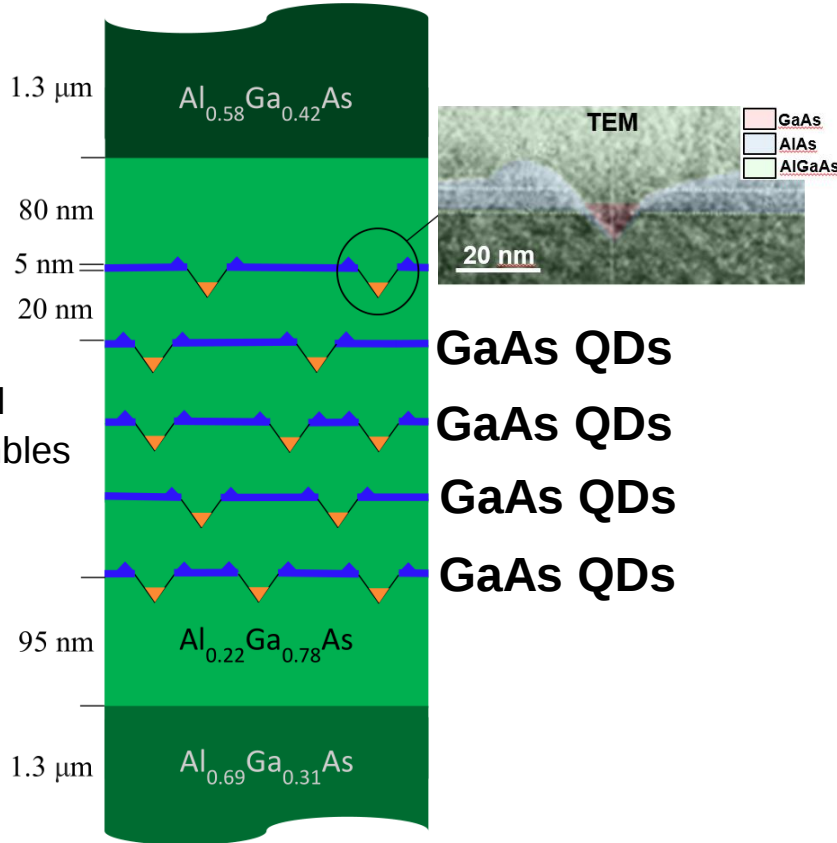
PL2 (simplified setup)

- Sample cooling down to 30 K
- Vibrations ≈ 10 μ m

INF18 - Photolumineszenz von Halbleiter-Quantenpunkten

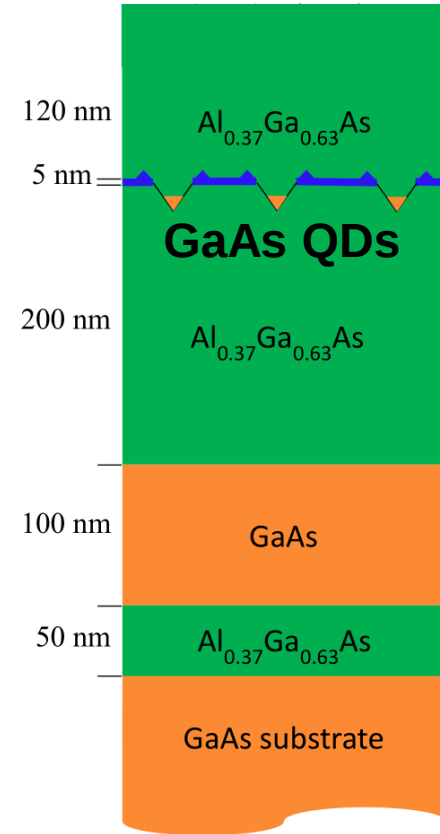
Samples A (special) 5 QD layers thick AlGaAs

- + High intensity
- + No GaAs signal
- Only QD ensembles



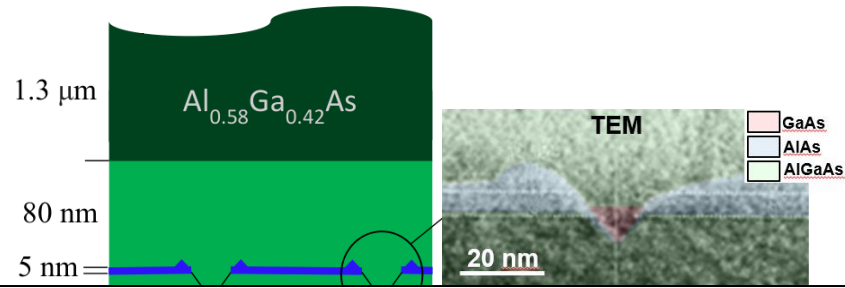
Samples B (standard) 1 QD layer thin AlGaAs

- Low intensity
- GaAs signal
- + Single QD PL

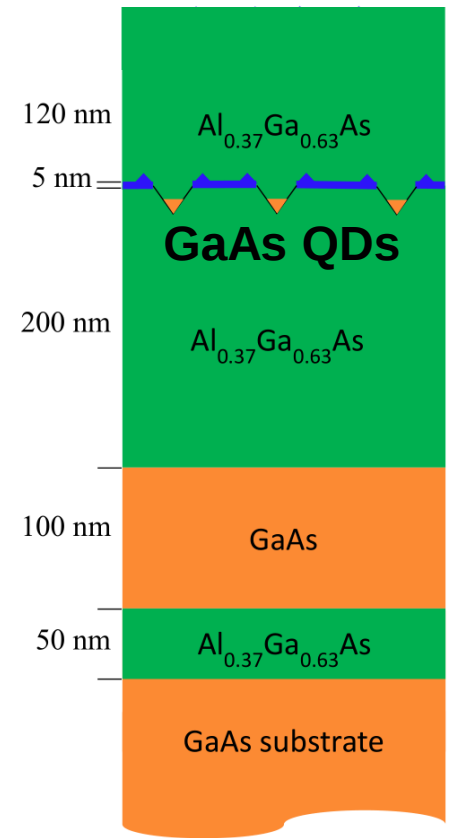


INF18 - Photolumineszenz von Halbleiter-Quantenpunkten

Samples A
 (special)
 5 QD layers
 thick AlGaAs



Samples B
 (standard)
 1 QD layer
 thin AlGaAs



- Low intensity
- GaAs signal
- + Single QD PL

Intensity

GaAs substrate (only samples B)

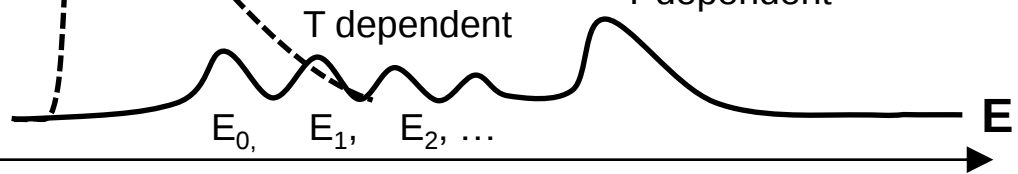
T dependent
 left: bandgap
 right: Fermi distribution

Al_xGa_{1-x}As barrier

x dependent
 T dependent

GaAs QDs

T dependent

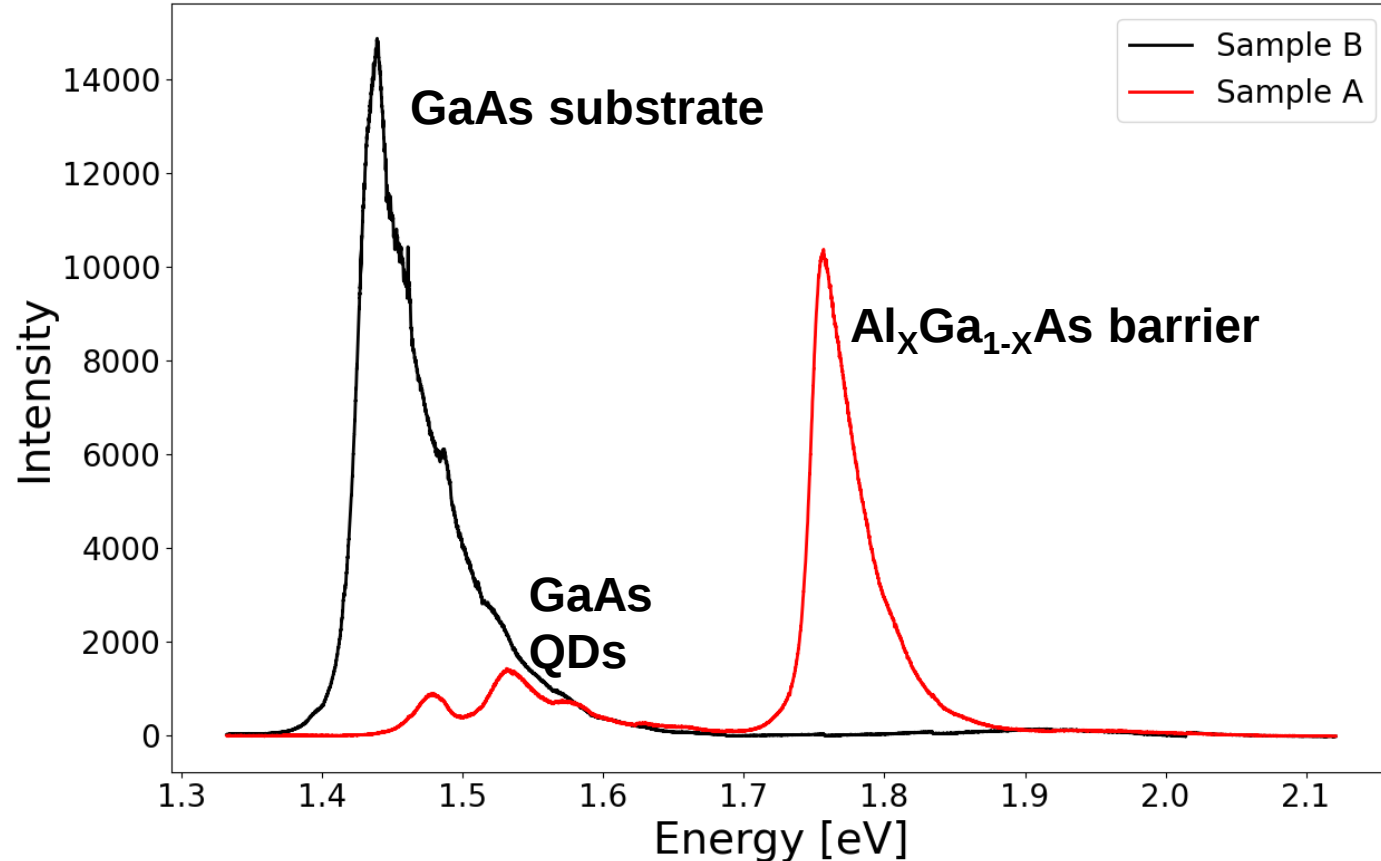


INF18 - Photolumineszenz von Halbleiter-Quantenpunkten

T = 300 K

Setup PL2

→ Sample design
QD shell structure



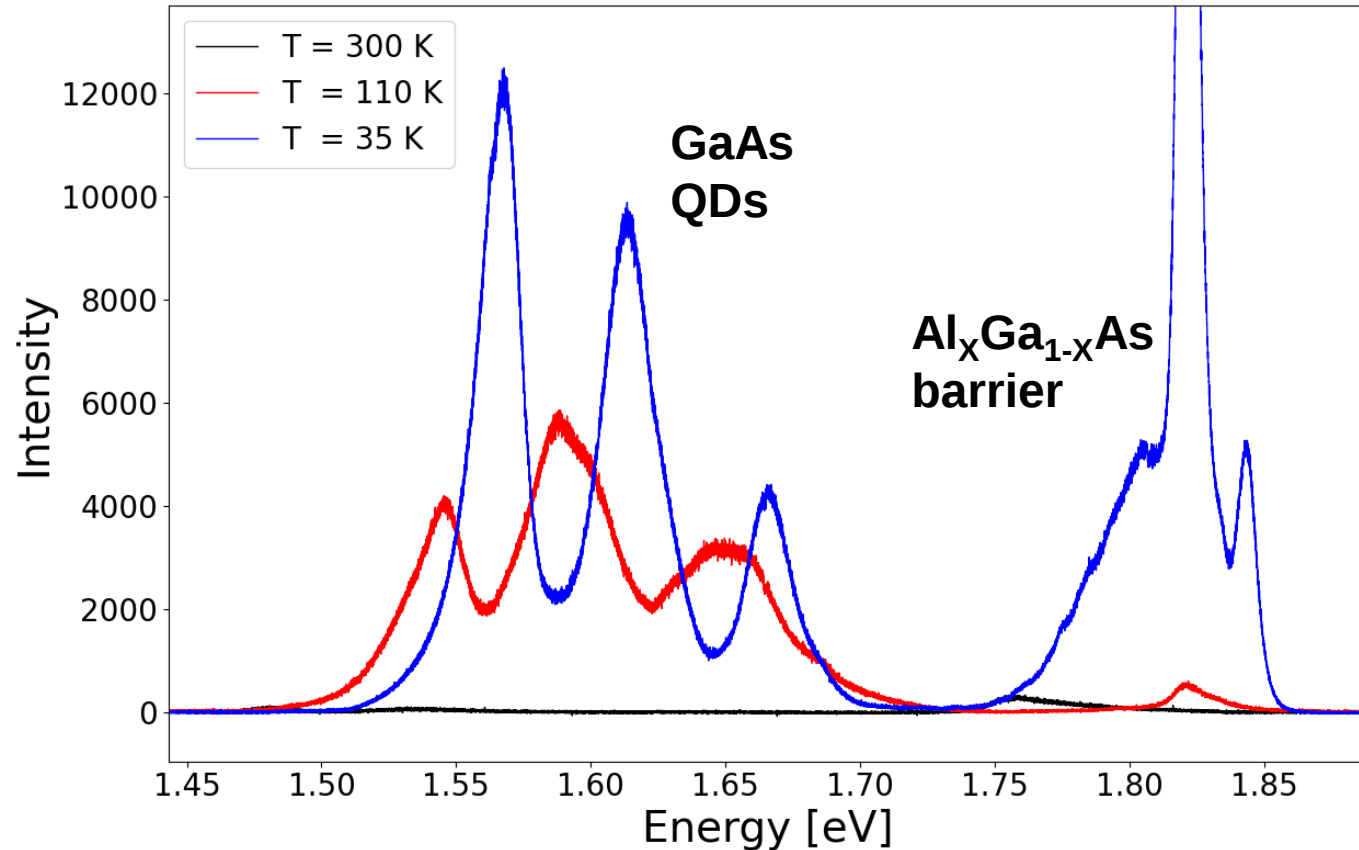
INF18 - Photolumineszenz von Halbleiter-Quantenpunkten

T varied

Sample A

Setup PL2

→ T dependence
of energy
and intensity



INF18 - Photolumineszenz von Halbleiter-Quantenpunkten

$T = 4 \text{ K}$

Laser power P varied

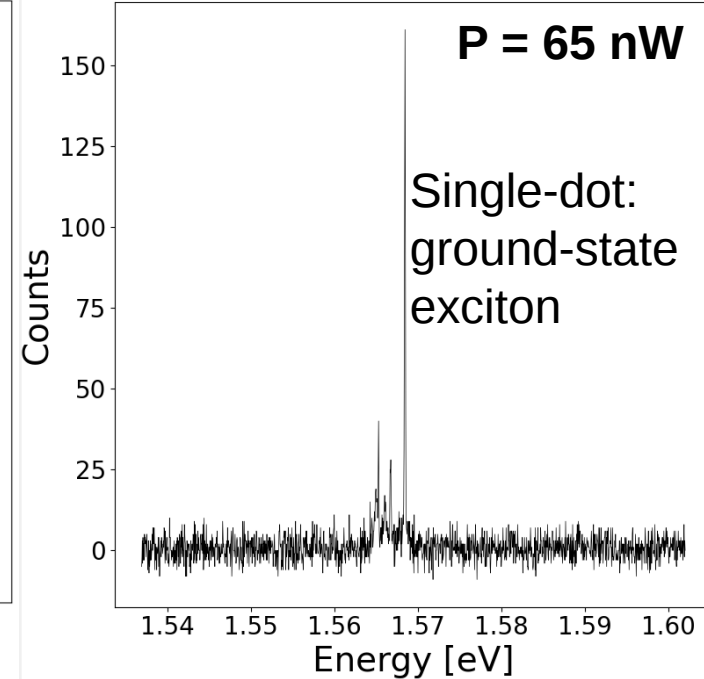
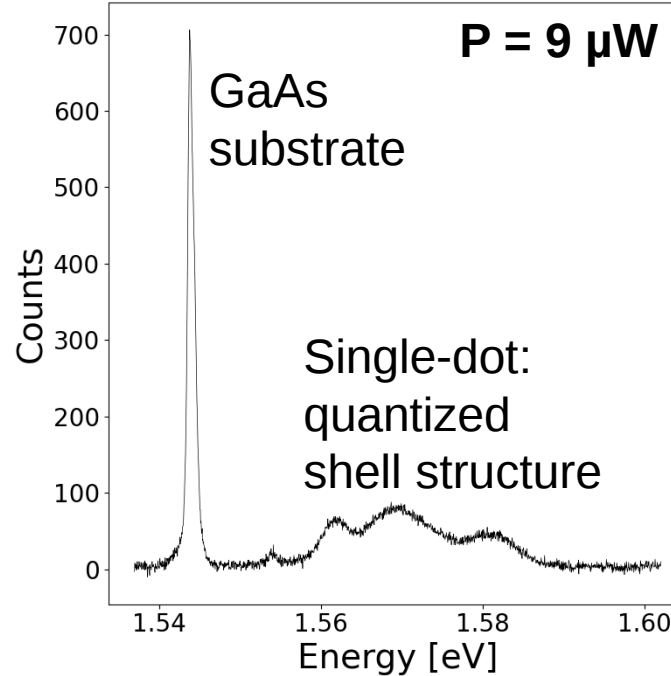
Sample B

Setup PL1

→ GaAs PL small
Single-dot PL
Single photons

Applications:

in quantum information technology QDs as deterministic source for single photons e.g. for quantum cryptography or photonic integrated circuits



Aim of the experiment, experimental part:

- Basics of optical spectroscopy: optical components, spectrometer, cryo-cooler
- Practical training on optical spectroscopy: adjustment, measurement of: single nanometer-sized objects, at cryogenic T, with single photon sensitivity
- Data acquisition: sensitivity, noise, parameter optimization strategies, errors

Data analysis:

- Basic understanding of semiconductors optics and semiconductor quantum dots
- Data interpretation from QDs as 3D quantum harmonic oscillator: electron and hole quantization energies, Coulomb-interaction, QD size
- Influence of sample design, temperature, excitation power, ...